

### General Description

This Trench MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for Back-light Inverter and power Supply.

### FEATURES

- $V_{DSS}=40V$ ,  $I_D=35A$ .
- Low Drain to Source On-state Resistance.
  - :  $R_{DS(ON)}=17.5m\Omega$  (Max.) @  $V_{GS}=10V$
  - :  $R_{DS(ON)}=27.0m\Omega$  (Max.) @  $V_{GS}=4.5V$

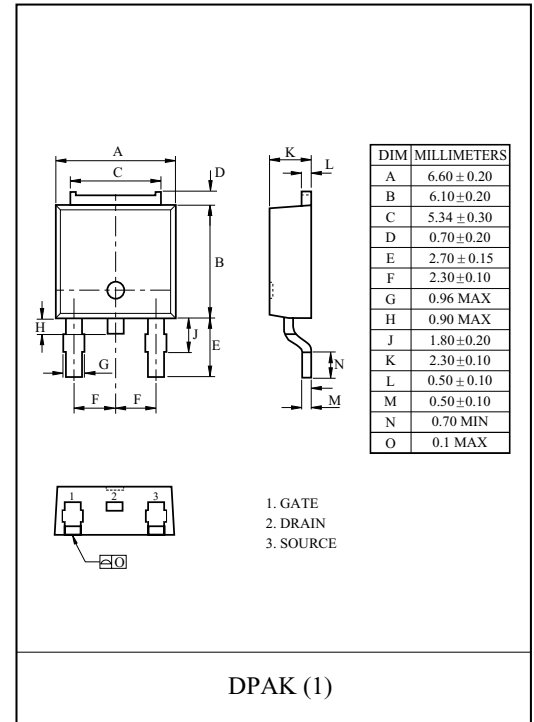
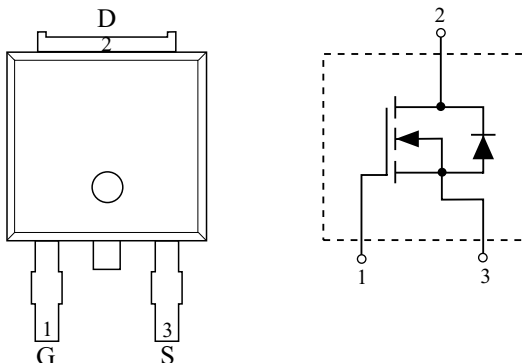
### MAXIMUM RATING (Ta=25°C Unless otherwise Noted)

CHARACTERISTIC		SYMBOL	N-Ch	UNIT
Drain to Source Voltage		$V_{DSS}$	40	V
Gate to Source Voltage		$V_{GSS}$	$\pm 20$	V
Drain Current	DC@ $T_C=25^\circ C$ (Note1)	$I_D$	35	A
	Pulsed (Note2)	$I_{DP}$	140	
Drain Power Dissipation	@ $T_C=25^\circ C$ (Note1)	$P_D$	42	W
	@ $T_a=25^\circ C$ (Note2)		3.1	
Maximum Junction Temperature		$T_j$	150	$^\circ C$
Storage Temperature Range		$T_{stg}$	-55 ~ 150	$^\circ C$
Thermal Resistance, Junction to Case (Note1)		$R_{thJC}$	3.0	$^\circ C/W$
Thermal Resistance, Junction to Ambient (Note2)		$R_{thJA}$	40	$^\circ C/W$

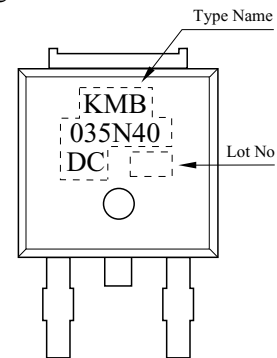
Note 1)  $R_{thJC}$  means that the infinite heat sink is mounted.

Note 2) Surface Mounted on  $1 \times 1$  Pad of 2 oz copper.

### PIN CONNECTION (TOP VIEW)



### Marking



# KMB035N40DC

## ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40	-	-	V
Drain Cut-off Current		I <sub>DSS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =32V	-	-	1	μA
Gate to Source Leakage Current		I <sub>GSS</sub>	V <sub>GS</sub> =± 20V, V <sub>DS</sub> =0V	-	-	± 100	nA
Gate to Source Threshold Voltage		V <sub>th</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	-	3	V
Drain to Source On Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =18A (Note3)	-	14.0	17.5	mΩ
			V <sub>GS</sub> =4.5V, I <sub>D</sub> =16A (Note3)	-	20.0	27.0	
Forward Transconductance		g <sub>fs</sub> *	V <sub>DS</sub> =5V, I <sub>D</sub> =18A (Note3)	-	35	-	S
<b>Dynamic</b>							
Input Capacitance		C <sub>iss</sub>	V <sub>DS</sub> =20V, f=1MHz, V <sub>GS</sub> =0V	-	524	-	pF
Output Capacitance		C <sub>oss</sub>		-	103	-	
Reverse Transfer Capacitance		C <sub>rss</sub>		-	51	-	
Gate Resistance		R <sub>g</sub>	f=1MHz	-	2.4	-	Ω
Total Gate Charge	V <sub>GS</sub> =10V	Q <sub>g</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =18A (Note3)	-	12.2	-	nC
	V <sub>GS</sub> =5V	Q <sub>g</sub>		-	6.3	-	
Gate to Source Charge		Q <sub>gs</sub>		-	1.9	-	
Gate to Drain Charge		Q <sub>gd</sub>		-	3.3	-	
Turn-On Delay Time		t <sub>d(on)</sub>		V <sub>DD</sub> =20V, V <sub>GS</sub> =10V I <sub>D</sub> =18A, R <sub>G</sub> =6Ω (Note3)	-	16	
Turn-On Rise Time		t <sub>r</sub>	-		18	-	
Turn-Off Delay Time		t <sub>d(off)</sub>	-		52	-	
Turn-Off Fall Time		t <sub>f</sub>	-		13	-	
<b>Source-Drain Diode Ratings</b>							
Continuous Source Current		I <sub>S</sub>	-	-	35	-	A
Rulsed Source Current		I <sub>SP</sub>	-	-	140	-	A
Source to Drain Forward Voltage		V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =3A (Note3)	-	0.8	1.2	V
Reverse Recovery time		t <sub>rr</sub>	I <sub>S</sub> =18A, dI/dt=100A/μs	-	22	-	ns
Reverse Recovered Charge		Q <sub>rr</sub>	I <sub>S</sub> =18A, dI/dt=100A/μs	-	8.6	-	nC
Note3) Pulse Test : Pulse width <300μs , Duty cycle < 2%							

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Fig1.  $I_D - V_{DS}$

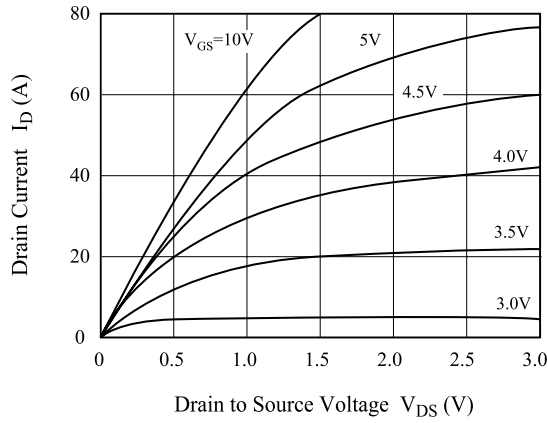


Fig2.  $R_{DS(on)} - I_D$

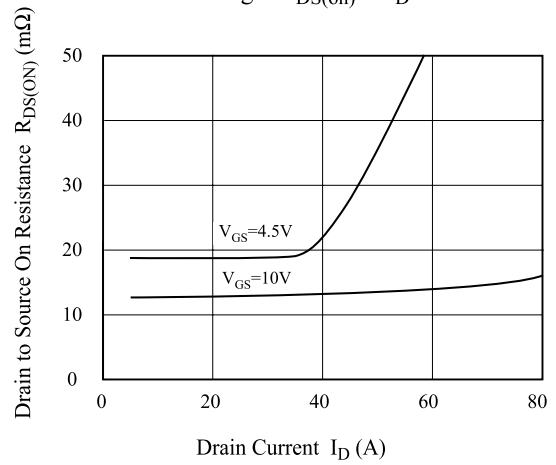


Fig3.  $I_D - V_{GS}$

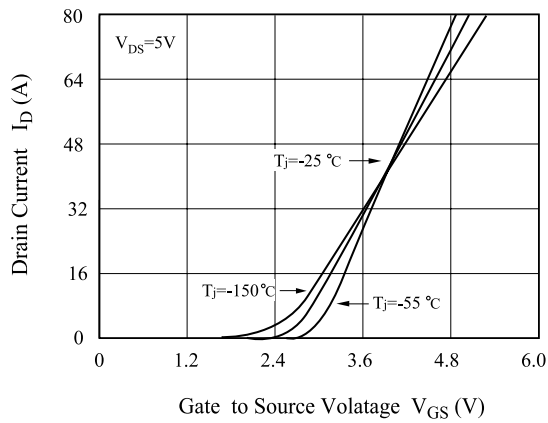


Fig4.  $R_{DS(on)} - T_j$

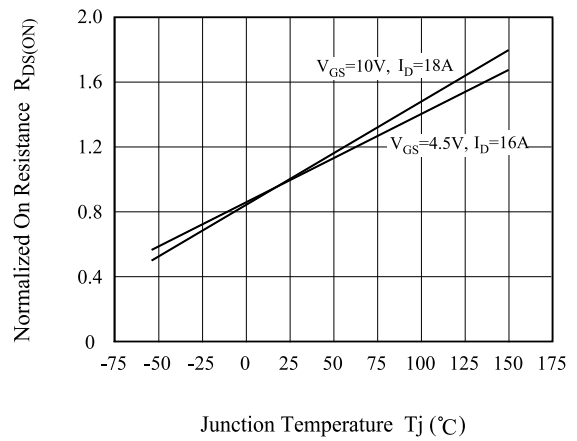


Fig5.  $V_{th} - T_j$

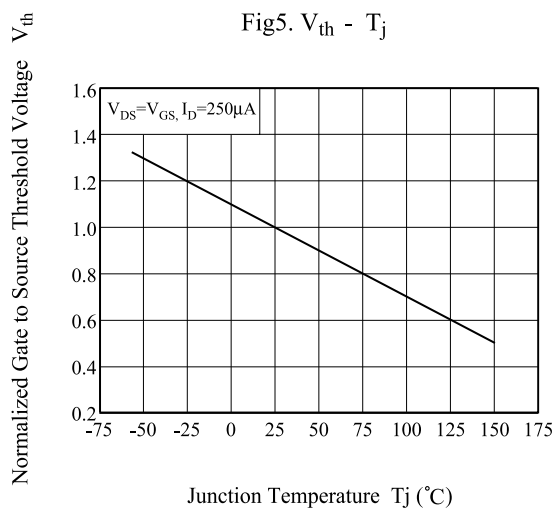
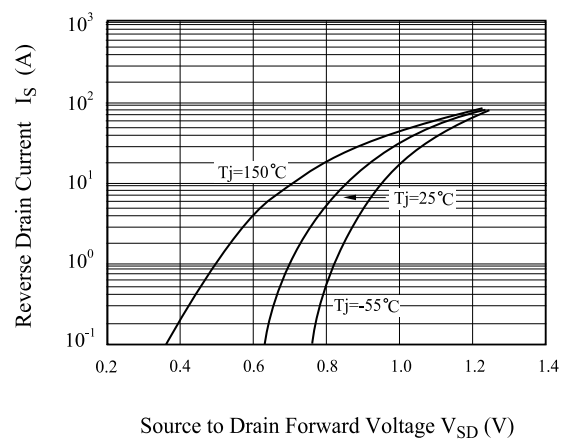


Fig6.  $I_S - V_{SD}$



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Fig7.  $R_{DS(on)}$  -  $V_{GS}$

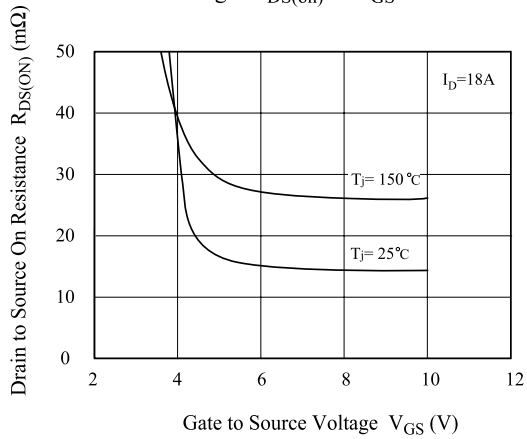


Fig 8. C -  $V_{DS}$

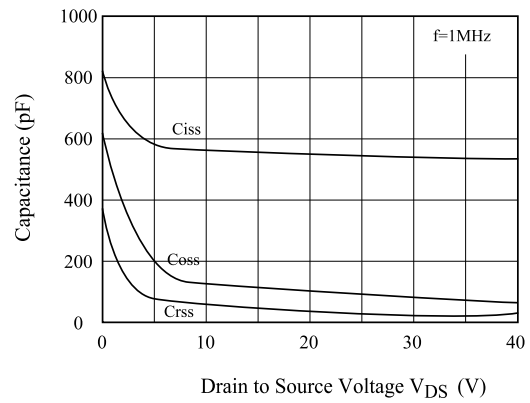


Fig 9.  $V_{GS}$  -  $Q_g$

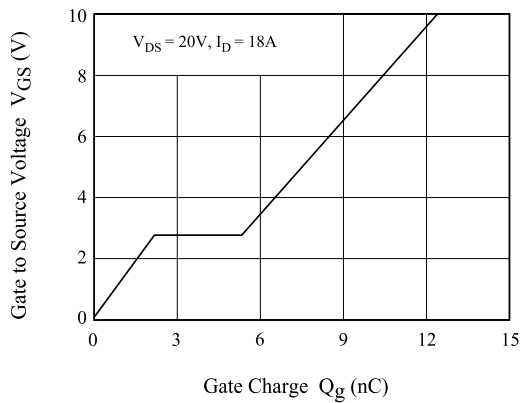


Fig10. Safe Operation Area

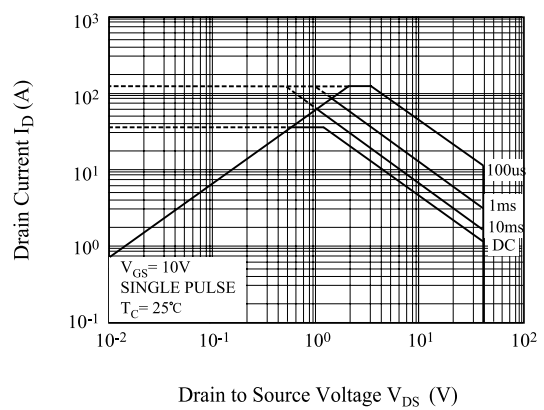


Fig11. Transient Thermal Response Curve

